

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	TTA1943
▶ Overseas	Part Number	TTA1943
▶ Equivalent	Part Number	TTA1943

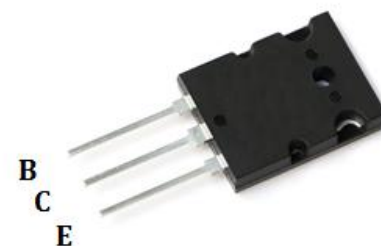
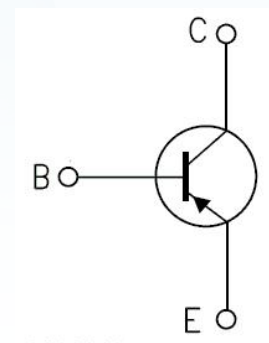
EV is the abbreviation of name EVVO

Silicon PNP transistor

Power Amplifier Applications

- Complementary to TTC5200
- High collector voltage: $V_{CEO} = -230V$ (min)
- Recommended for 100-W high-fidelity audio frequency amplifier Output stage

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



TO-3PL

Absolute Maximum Ratings($T_c=25^{\circ}C$):

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-230	V
Collector-emitter voltage	V_{CEO}	-230	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-15	A
Base current	I_B	-1.5	A
Collector power dissipation ($T_c=25^{\circ}C$)	P_C	150	W
Junction temperature	T_J	150	$^{\circ}C$
Storage temperature range	T_{STG}	-55~150	$^{\circ}C$

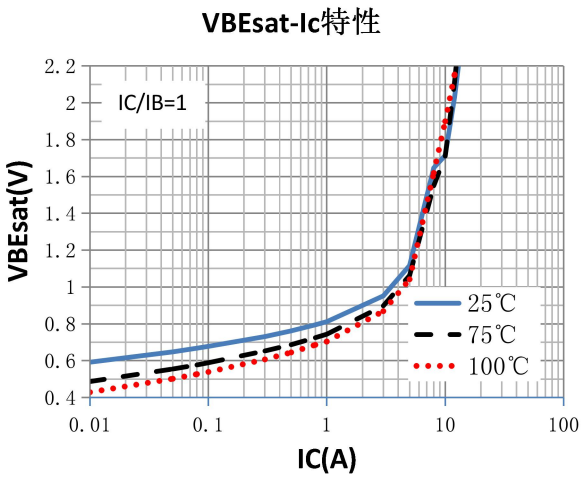
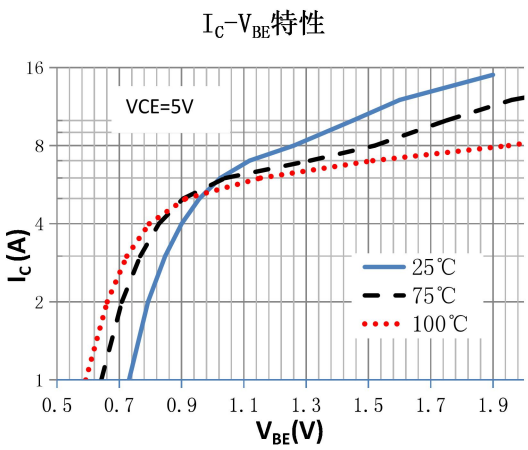
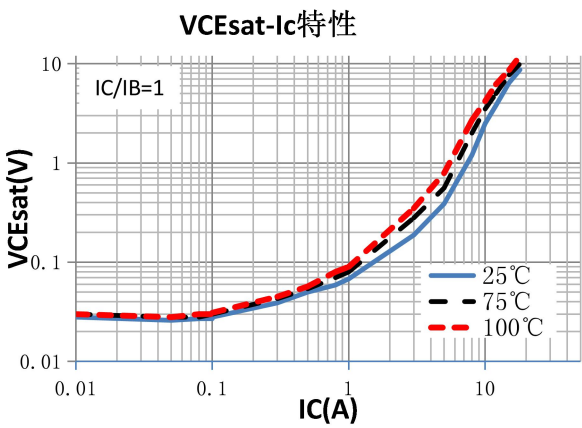
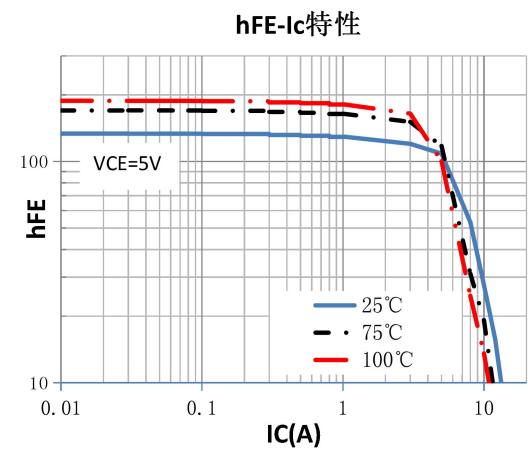
Electrical Characteristics (Tc=25℃):

Silicon PNP transistor

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Collector cut-off current	ICBO	V _{CB} =-230V; I _E =0			-10.0	uA
Emitter cut-off current	IEBO	V _{EB} =-5V; I _C =0			-10.0	uA
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-50mA; I _B =0	-230			V
DC current gain	h _{FE}	I _C =-5A; V _{CE} =-1V	80		160	
	h _{FE(2)}	I _C =-5A; V _{CE} =-7V	35			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-8A; I _B =-0.8A			-3.0	V
Base-emitter voltage	V _{BE}	V _{CE} =-5V; I _C =-7A			-1.5	V
Transition frequency	f _T	V _{CE} =-5V; I _C =-1A		30		MHz

Symbol	Paramter	Typ	Units
R _{θJC}	Junction-to-Case	0.35	℃/W

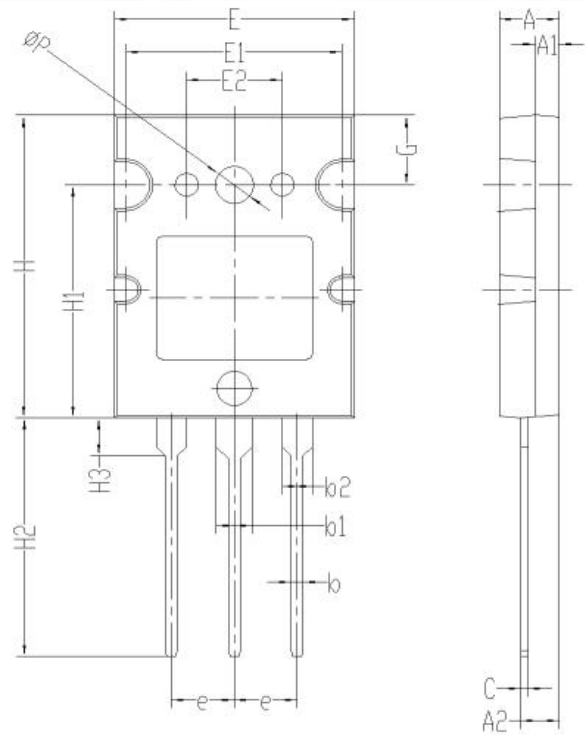
TYPICAL CHARACTERISTICS



Package Information

Silicon PNP transistor

TO-3PL PACKAGE



Symbol	Dimensions (millimeters)	
	Min.	Max.
A	4.80	5.20
A1	1.80	2.20
A2	3.00	3.40
b	0.80	1.20
b1	2.80	3.20
b2	2.30	2.70
c	0.40	0.80
e	5.25	5.65
E	19.8	20.2
E1	17.8	18.2
E2	7.8	8.2
H	25.8	26.2
H1	19.8	20.2
H2	20.0	21.0
H3	3.05	3.45
G	5.80	6.20
ΦP	3.10	3.50
J	4.80	5.20
K	1.80	2.20

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